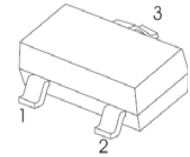


**SOT-23 Plastic-Encapsulate Transistors**
**FEATURES**

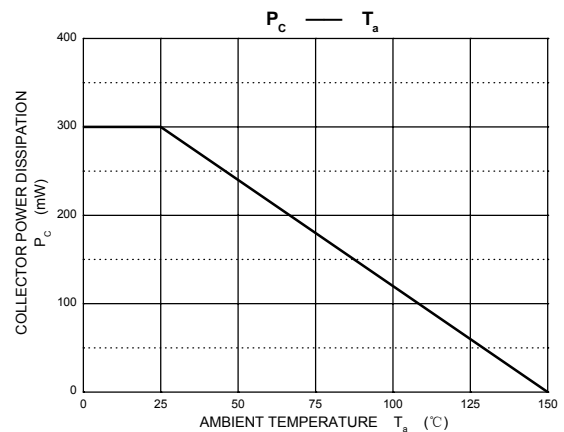
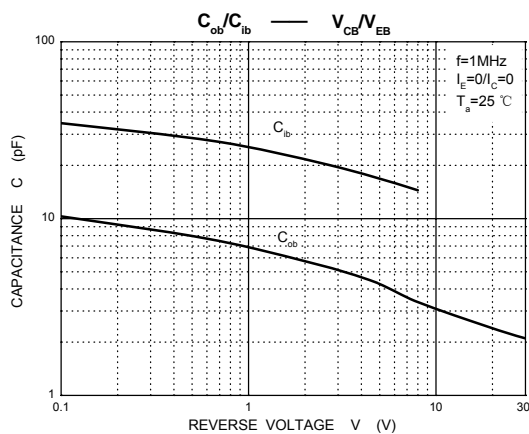
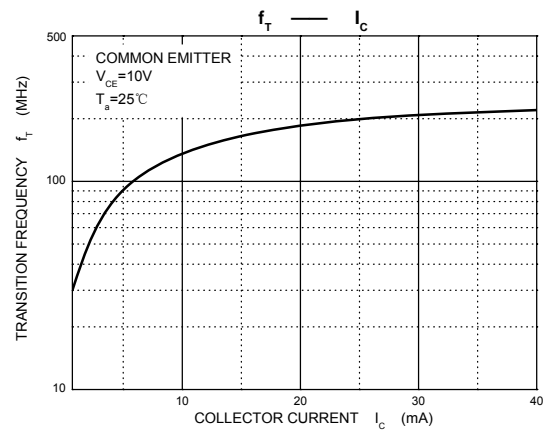
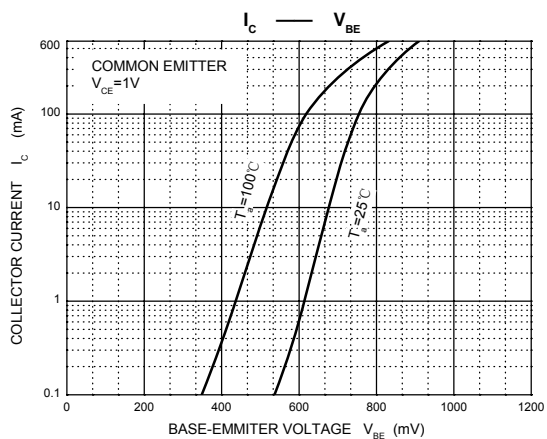
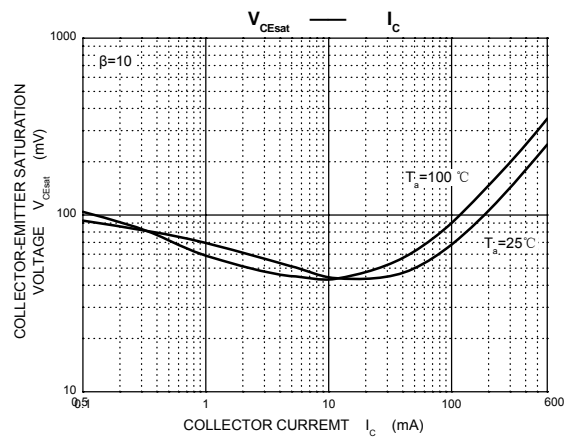
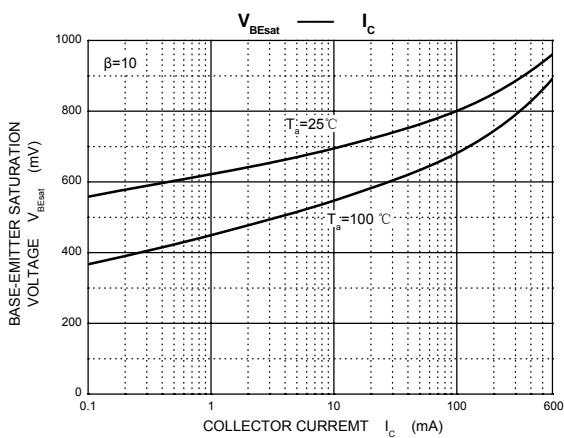
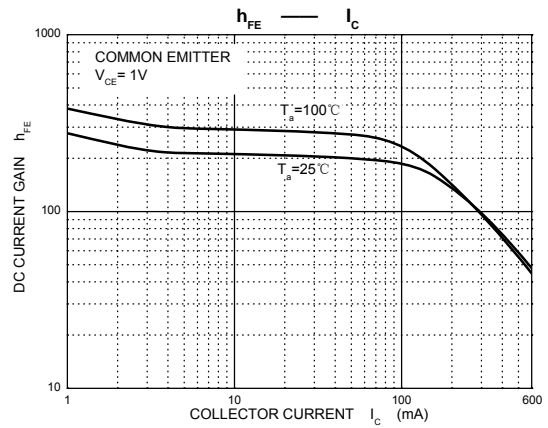
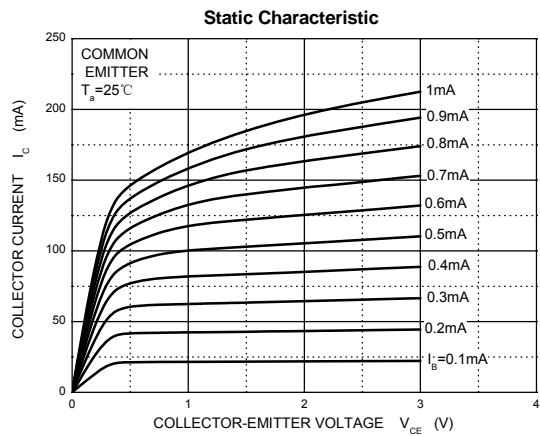
- Switching Transistor

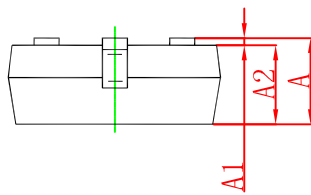
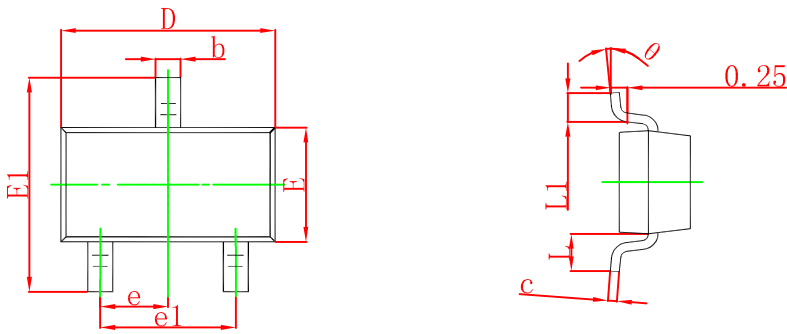
**MARKING:2X**
**SOT - 23**

**1. BASE**
**2. EMITTER**
**3. COLLECTOR**
**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current	600	mA
P <sub>C</sub>	Collector Power Dissipation	300	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	417	°C/W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

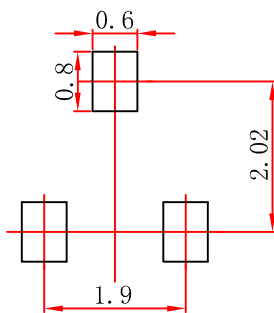
**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =100 μ A, I <sub>E</sub> =0	60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	40			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =100 μ A, I <sub>C</sub> =0	6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =50V, I <sub>E</sub> =0			0.1	μ A
Collector cut-off current	I <sub>CEX</sub>	V <sub>CE</sub> =35V, V <sub>EB</sub> =0.4V			0.1	μ A
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			0.1	μ A
DC current gain	h <sub>FE1</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =0.1mA	20			
	h <sub>FE2</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =1mA	40			
	h <sub>FE3</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =10mA	80			
	h <sub>FE4</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =150mA	100		300	
	h <sub>FE5</sub>	V <sub>CE</sub> =2V, I <sub>C</sub> =500mA	40			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA			0.4	V
		I <sub>C</sub> =500mA, I <sub>B</sub> =50mA			0.75	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA			0.95	V
		I <sub>C</sub> =500mA, I <sub>B</sub> =50mA			1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =20mA, f=100MHz	250			MHz
Delay time	t <sub>d</sub>	V <sub>CC</sub> =30V, V <sub>BE(off)</sub> =-2V			15	ns
Rise time	t <sub>r</sub>	I <sub>C</sub> =150mA, I <sub>B1</sub> =15mA			20	ns
Storage time	t <sub>s</sub>	V <sub>CC</sub> =30V, I <sub>C</sub> =150mA			225	ns
Fall time	t <sub>f</sub>	I <sub>B1</sub> =I <sub>B2</sub> =15mA			60	ns

**Typical Characteristics**




Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

**SOT-23 Suggested Pad Layout**


- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.05\text{mm}$ .
  3. The pad layout is for reference purposes only.